METHOD FOR IMPROVING HARD BIAS PROPERTIES OF LAYERS IN A MAGNETORESISTIVE SENSOR

ABSTRACT

A method for improving hard bias properties of layers of a magnetoresistance sensor is disclosed. Properties of the hard bias layer are improved using a seedlayer structure that includes at least a first layer of silicon and a second layer comprising chromium or chromium molybdenum. Further, benefits are achieved when the seedlayer structure includes a layer of tantalum.